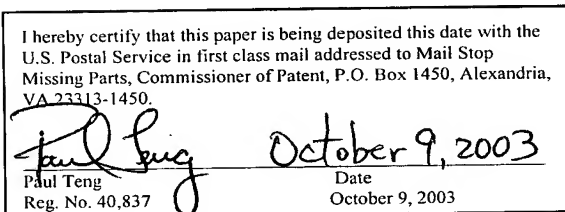




PATENT  
Dkt. 2271/62289-Z

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Application of: Seiji SARAYAMA et al.  
Serial No. : 10/601,301 Group Art Unit: 1765  
Date Filed : June 13, 2003 Examiner:  
For : PRODUCTION OF A GaN BULK CRYSTAL SUBSTRATE AND  
A SEMICONDUCTOR DEVICE FORMED ON A GaN BULK  
CRYSTAL SUBSTRATE



1185 Avenue of the Americas  
New York, New York 10036  
(212) 278-0400  
October 9, 2003

**RESPONSE TO "NOTICE TO FILE CORRECTED APPLICATION PAPERS" AND  
REQUEST FOR CORRECTED FILING RECEIPT**

Mail Stop Missing Parts  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 23313-1450

Sir:

In response to the Notice to File Corrected Application Papers-Filing Date Granted dated September 15, 2003, applicants hereby submit (1) copy of the Notice, and (2) two sets of formal drawings, Figs. 1-21.

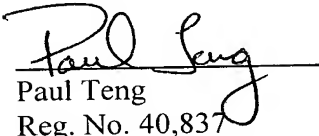
Applicants also enclose a copy of the official filing receipt, which erroneously states the title as: -Production of a GaN bulk crystal substrate and a semiconductor device formed on a GuN bulk crystal substrate-, rather than -Production of a GaN bulk crystal substrate and

a semiconductor device formed on a ~~GaN~~ GaN bulk crystal substrate--.

Applicants hereby respectfully request that a corrected filing receipt be issued showing the correct title.

No fee is believed to be due. However, please charge any additional fees or credit any overpayment to our deposit account number 03-3125. A copy of this sheet is enclosed.

Respectfully submitted,

  
Paul Teng  
Reg. No. 40,837

Encls.